

2SB566(K), 2SB566A(K)

Silicon PNP Triple Diffused

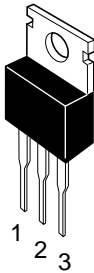
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Application

Low frequency power amplifier power switching complementary pair with 2SD476(K) and 2SD476A(K)

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings		Unit
		2SB566(K)	2SB566A(K)	
Collector to base voltage	V_{CBO}	-70	-70	V
Collector to emitter voltage	V_{CEO}	-50	-60	V
Emitter to base voltage	V_{EBO}	-5	-5	V
Collector current	I_C	-4	-4	A
Collector peak current	$I_{C(peak)}$	-8	-8	A
Collector power dissipation	P_C^{*1}	40	40	W
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-55 to +150	°C

Note: 1. Value at $T_C = 25^\circ\text{C}$.

2SB566(K), 2SB566A(K)

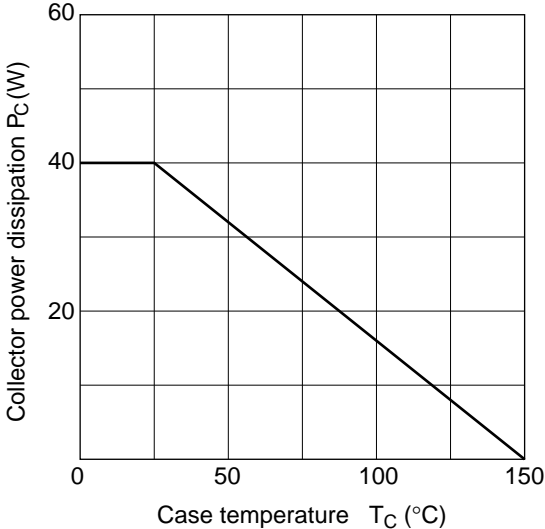
Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SB566(K)			2SB566A(K)			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-70	—	—	-70	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-50	—	—	-60	—	—	V	$I_C = -50 mA, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-1	—	—	-1	μA	$V_{CB} = -50 V, I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	200	60	—	200		$V_{CE} = -4 V, I_C = -1 A$
	h_{FE2}	35	—	—	35	—	—		$V_{CE} = -4 V, I_C = -0.1 A$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-1.0	—	—	-1.0	V	$I_C = -2 A, I_B = -0.2 A$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	-1.2	—	—	-1.2	V	$I_C = -2 A, I_B = -0.2 A$
Gain bandwidth product	f_T	—	15	—	—	15	—	MHz	$V_{CE} = -4 V, I_C = -0.5 A$
Turn on time	t_{on}	—	0.3	—	—	0.3	—	μs	$V_{CC} = -10.5 V$
Turn off time	t_{off}	—	3.0	—	—	3.0	—	μs	$I_C = 10I_{B1} = -10I_{B2} =$
Storage time	t_{stg}	—	2.5	—	—	2.5	—	μs	-0.5 A

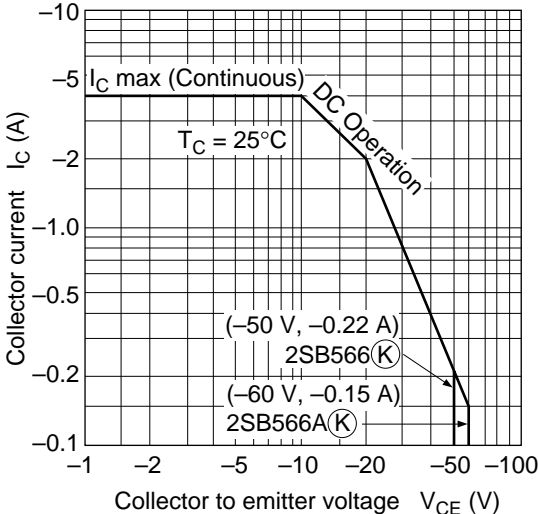
Note: 1. The 2SB566(K) and 2SB566A(K) are grouped by h_{FE1} as follows.

B	C
60 to 120	100 to 200

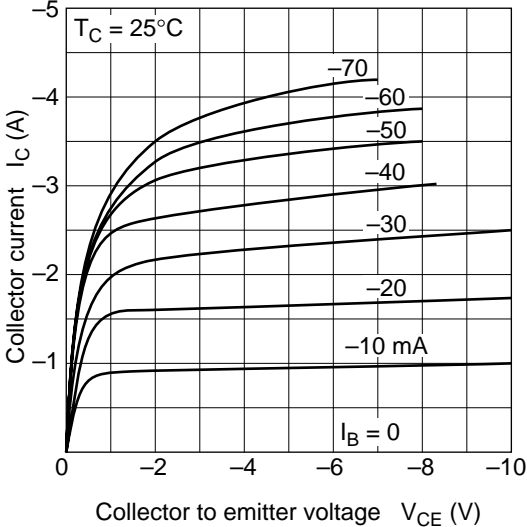
Maximum Collector Dissipation Curve



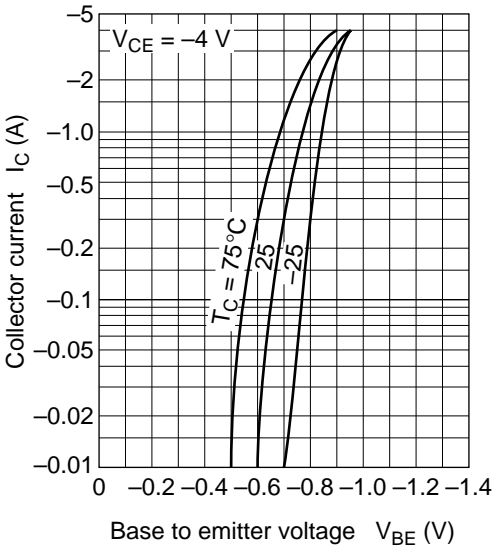
Area Safe Operation



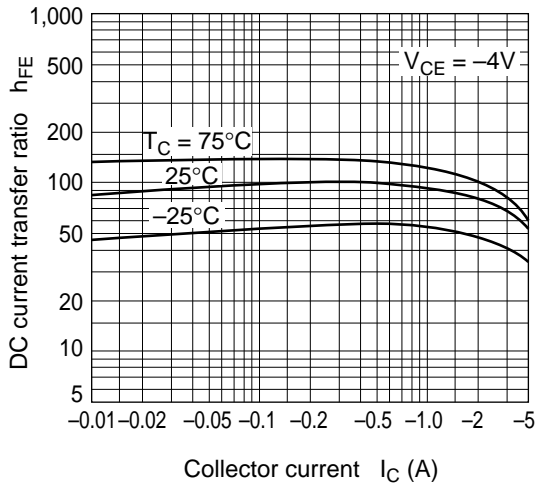
Typical Output Characteristics



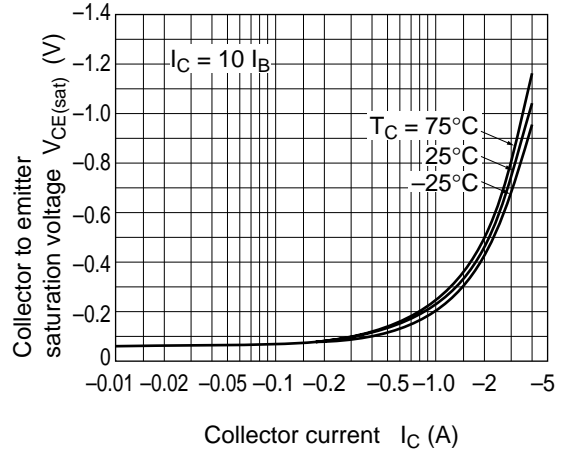
Typical Transfer Characteristics

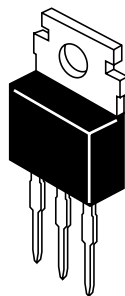
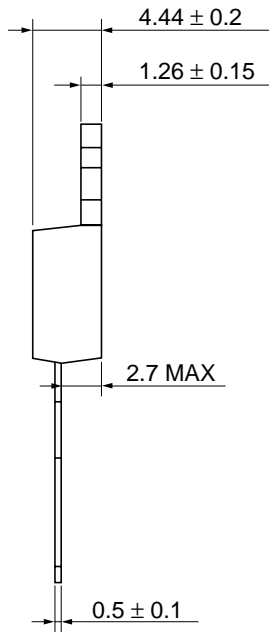


DC Current Transfer Ratio
vs. Collector Current



Collector to Emitter Saturation Voltage
vs. Collector Current





Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

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